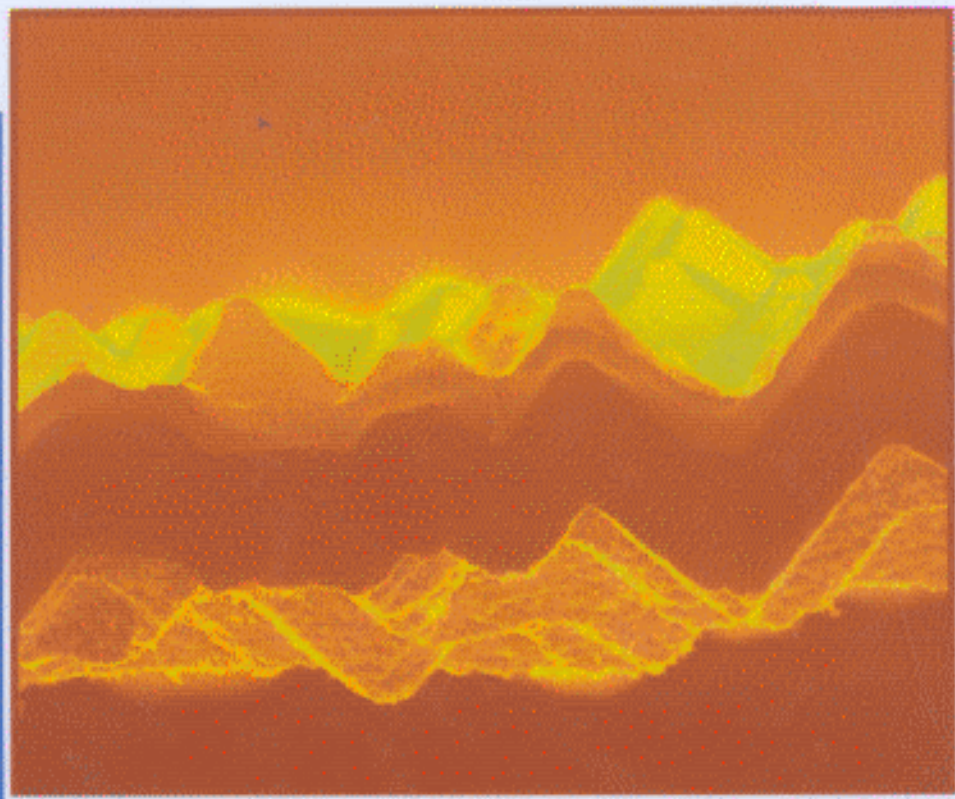


Rolf Brendel

Thin-Film Crystalline Silicon Solar Cells

Physics and Technology



WILEY-VCH

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